

BAW56LT1

Preferred Device

Monolithic Dual Switching Diode Common Anode

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Non-Repetitive Peak Forward Current $t = 1 \mu s$ (Note 3)	I_{FSM}	4	A

THERMAL CHARACTERISTICS

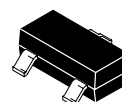
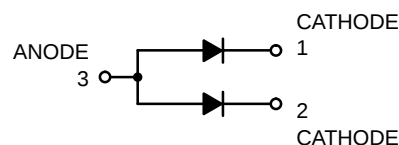
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ C$ Derate above $25^\circ C$	P_D	225	mW
		1.8	mW/ $^\circ C$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ C/W$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ C$ Derate above $25^\circ C$	P_D	300	mW
		2.4	mW/ $^\circ C$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ C/W$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ C$

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
3. Square Wave; $T_J = 25^\circ C$.



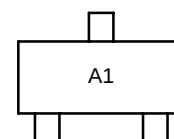
ON Semiconductor®

<http://onsemi.com>



SOT-23(TO-236)
CASE 318
Style 12

MARKING DIAGRAM



A1 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping [†]
BAW56LT1	SOT-23	3000 / Tape & Reel
BAW56LT3	SOT-23	10,000 / Tape & Reel

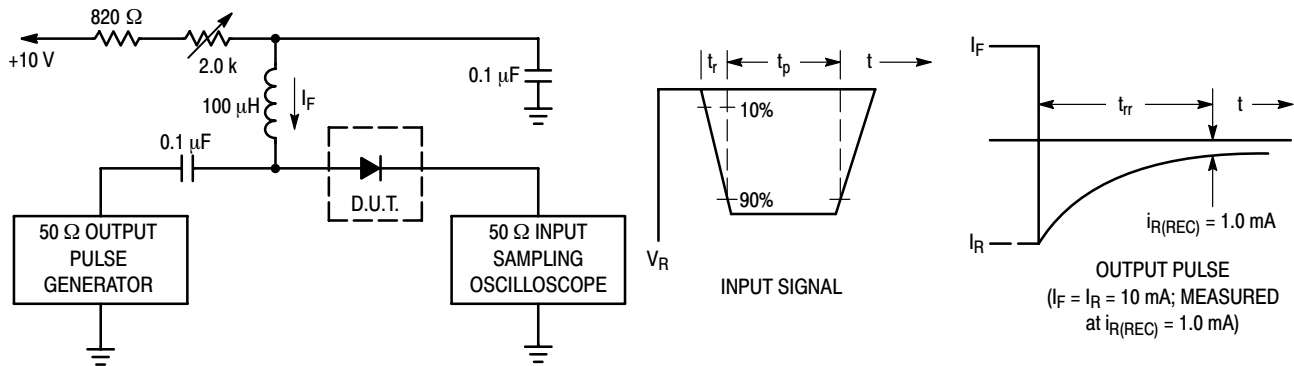
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

BAW56LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{BR} = 100 \mu\text{A}$)	$V_{(BR)}$	70	–	Vdc
Reverse Voltage Leakage Current ($V_R = 25 \text{ Vdc}$, $T_J = 150^\circ\text{C}$) ($V_R = 70 \text{ Vdc}$) ($V_R = 70 \text{ Vdc}$, $T_J = 150^\circ\text{C}$)	I_R	– – –	30 2.5 50	μA
Diode Capacitance ($V_R = 0$, $f = 1.0 \text{ MHz}$)	C_D	–	2.0	pF
Forward Voltage ($I_F = 1.0 \text{ mA}$) ($I_F = 10 \text{ mA}$) ($I_F = 50 \text{ mA}$) ($I_F = 150 \text{ mA}$)	V_F	– – – –	715 855 1000 1250	mVdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}$, $I_{R(REC)} = 1.0 \text{ mA}$) (Figure 1) $R_L = 100 \Omega$	t_{rr}	–	6.0	ns



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

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Curves Applicable to Each Cathode

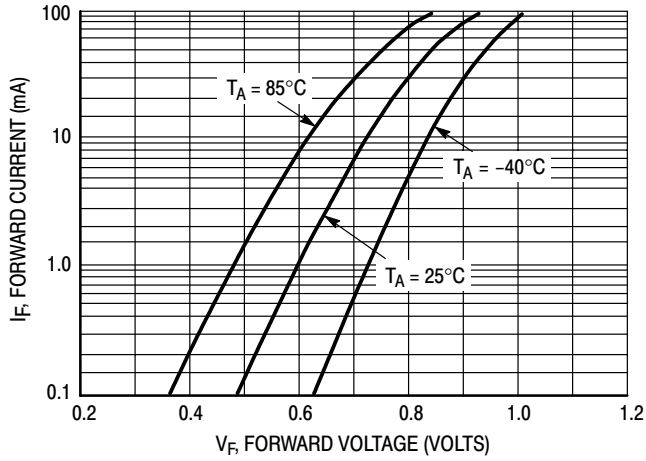


Figure 2. Forward Voltage

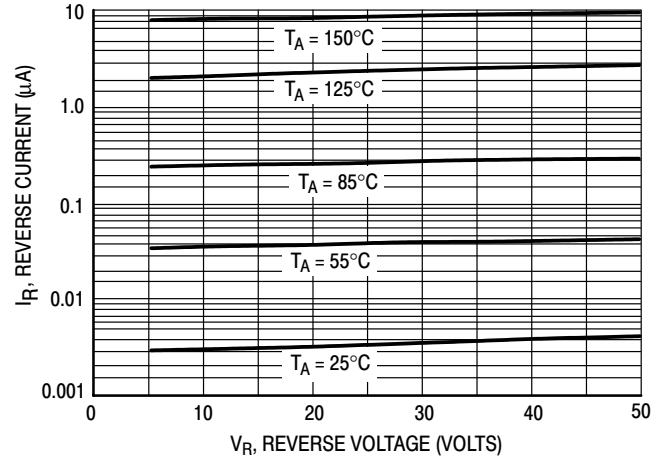


Figure 3. Leakage Current

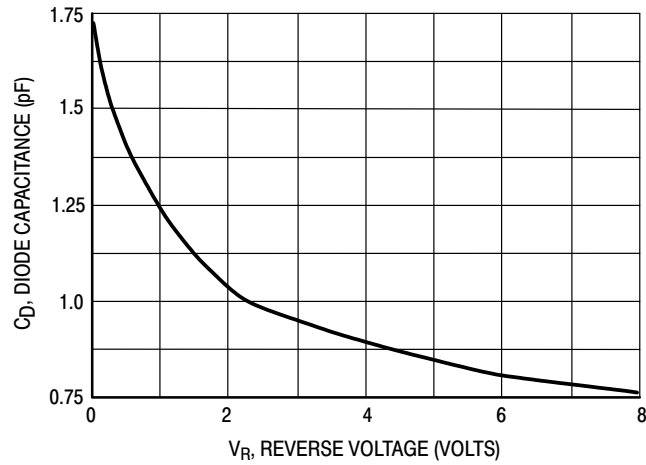


Figure 4. Capacitance

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PACKAGE DIMENSIONS

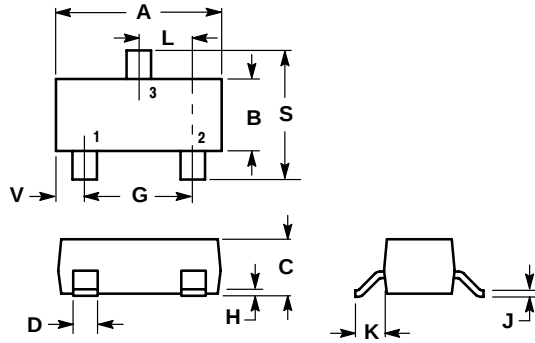
SOT-23-3 (TO-236)

CASE 318-08

ISSUE AH

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

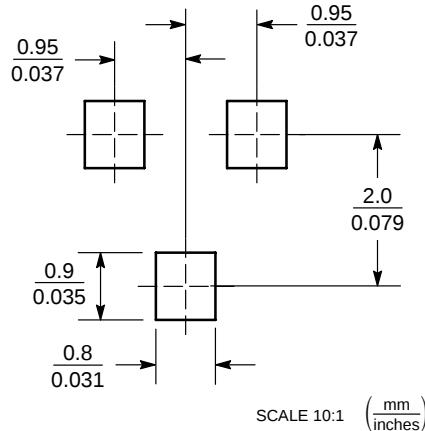


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 12:

1. CATHODE
2. CATHODE
3. ANODE

SOLDERING FOOTPRINT



SCALE 10:1 (mm/inches)

SOT-23-3

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